

# MONOLITHICALLY INTEGRATED $\mu$ PID ON $\mu$ COLUMNS FOR ULTRACOMPACT MICRO-GAS CHROMATOGRAPHY

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## ABSTRACT

This report describes a monolithically integrated microfluidic photoionization detector ( $\mu$ PID) on a microfabricated gas chromatography ( $\mu$ GC) column via wafer-level batch processing based on a silicon-on-insulator (SOI) architecture. The integrated chip enables an ultracompact (0.9 liters and 0.9 kg), fully automated, and battery-operated  $\mu$ GC system. Rapid separation of seven volatile organic compounds (VOCs) in  $\sim 2$  min at room temperature is demonstrated.

## KEYWORDS

Microfabricated gas chromatography, monolithic integration, photoionization detector

## INTRODUCTION

Microfabricated gas chromatography ( $\mu$ GC) has enabled portable, low-power, and rapid analysis across a diverse fields, such as industrial, biomedical, and environmental applications [1]. Most  $\mu$ GC devices currently employ hybrid integration, connecting components through off-chip interconnects (e.g., capillary guard columns). Monolithic integration offers key advantages, including enhanced system robustness, reduced human error, lower labor, minimized cold spots and dead volumes, and cost savings through batch fabrication. This work focuses on the integration of a separation micro-columns ( $\mu$ columns) and a detector onto a single chip.

Among sensor types, integrated photoionization detector (PID) has proven superior due to its rapid response and high sensitivity [2, 3]. However, state-of-the-art integrated PIDs suffer from drawbacks, such as reliance on bulky helium cartridges, co-planar collection electrodes, and single-die microfabrication processes [2, 3]. In contrast, advanced standalone microfluidic PIDs ( $\mu$ PIDs) feature parallel-plate electrodes, operate without auxiliary gases, and achieve parts-per-trillion (ppt) sensitivity with a six-order linear dynamic range [4, 5].

This paper presents a microfabrication process for monolithic integration of such a  $\mu$ PID with a  $\mu$ column batched-processed on a wafer scale. A new integrated device architecture of  $\mu$ PID on  $\mu$ column (i.e., integrated column-PID (iCPID)) is introduced based on silicon-on-insulator (SOI) structure. The buried oxide (BOX) provides electrical insulation between the  $\mu$ PID and  $\mu$ column, and its etch-through part serves as vertical microfluidic vias for fluidic connections between two components. This enables monolithic integration of a vacuum-UV lamp-based parallel-plate  $\mu$ PID on a  $\mu$ column with embedded on-chip heater, all achieved through wafer-scale batch process. We also demonstrate an ultracompact  $\mu$ GC system design

based on iCPID.

## DESIGN AND WORKING PRINCIPLE

As illustrated in Figure 1, the iCPID is based on an SOI platform with a vertical stacking architecture, where the  $\mu$ PID resides on top of the  $\mu$ column. There are two etched-through vertical holes (i.e., microfluidic via) at the inlet and outlet of the  $\mu$ PID. They fluidically connect the  $\mu$ PID and  $\mu$ column, while the BOX electrically isolating them on SOI. A glass layer is anodically bonded to the SOI to seal the  $\mu$ column. The heater of  $\mu$ column is patterned on the same layer as the  $\mu$ PID with an additional layer of  $\text{SiO}_2$  for electrical isolation. A VUV lamp (Krypton for 10.6 eV) is hermetically mounted on the  $\mu$ PID by epoxy and for photoionization.

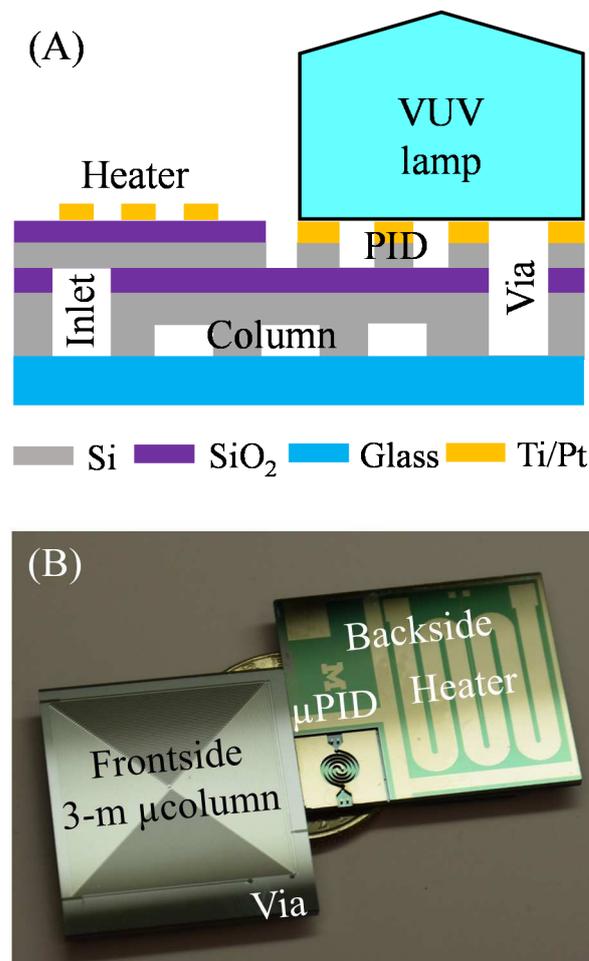


Figure 1: (A) Device architecture of iCPID. The iCPID is constructed on a silicon-on-insulator (SOI) structure. Device layer (backside) is designated for heater and  $\mu$ PID. Handle layer (frontside) is designated for  $\mu$ column where a glass substrate is capped on the SOI. A vacuum-UV

(VUV) lamp is hermetically sealed by UV epoxy on  $\mu$ PID and microfluidic vias. (B) Photograph of iCPID dies (left: 3-m  $\mu$ column side up; right:  $\mu$ PID and heater side up).

## FABRICATION

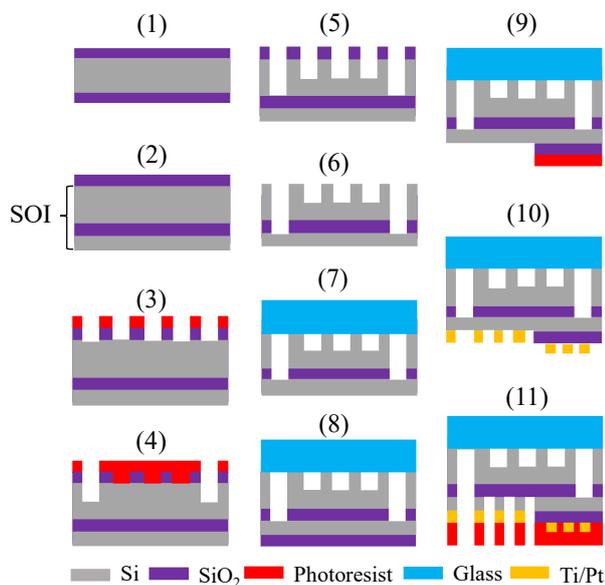


Figure 2: Microfabrication processes of iCPID. (1) Thermal oxidation; (2) Fusion bonding; (3)  $\text{SiO}_2$  RIE (reactive ion etching); (4) Si DRIE (deep-RIE); (5) Si DRIE (hard mask); (6) HF (hydrofluoric acid) strip; (7) Anodic bonding; (8) PECVD (plasma enhanced chemical vapor deposition)  $\text{SiO}_2$ ; (9)  $\text{SiO}_2$  RIE; (10) Evaporation and liftoff; (11) Si DRIE.

The monolithic microfabrication process for the iCPID is outlined in Figure 2. The handle wafer was thermalized with 2  $\mu\text{m}$  thermal oxide first. Both wafers first underwent RCA clean. After a dielectric barrier discharge (DBD) of atmospheric  $\text{N}_2$  plasma treatment on the bonding side of both wafers, a 400  $\mu\text{m}$  thick, double-side polished Si wafer ( $<100>$ , p-type, 0.001-0.005  $\Omega\cdot\text{cm}$ ) was fusion bonded to a 400  $\mu\text{m}$  thick, double-side polished Si wafer ( $<100>$ , p-type, 1-10  $\Omega\cdot\text{cm}$ ) with 2  $\mu\text{m}$  thick thermal oxide under vacuum at 400 $^\circ\text{C}$  and 20 MPa for 4 hours to generate the SOI wafer where the conductive wafer serves as the device layer and the insulating wafer serves as the handle wafer. The oxide on the handle layer was then patterned to create a hard mask for the  $\mu$ column, inlets and pass-through microfluidic vias. Next, photolithography was used to selectively expose the inlets and pass-through vias for a deep reactive-ion etching (DRIE) etch of  $\sim 150$   $\mu\text{m}$  in depth. The photoresist was then stripped and DRIE continued with the hard mask to simultaneously etch the  $\mu$ column to a final depth of 250  $\mu\text{m}$  while the inlets and pass-through vias were etched to the buried oxide layer (BOX) with the final depth of 400  $\mu\text{m}$ . After stripping the thermal oxide and BOX on the pass-through vias with HF, the handle layer was anodically bonded to a 550  $\mu\text{m}$  thick borofloat glass wafer to seal the  $\mu$ column. Next, 1  $\mu\text{m}$  of  $\text{SiO}_2$  was deposited on the device layer by plasma-enhanced chemical vapor deposition (PECVD) and the area where the  $\mu$ PID resides was etched away by RIE. A layer

of Ti/Pt (30/360 nm) was patterned on the device layer using lithography, evaporation, and liftoff to define the  $\mu$ PID electrodes and  $\mu$ column heater simultaneously. Finally, DRIE was used for generating the  $\mu$ PID. The  $\mu$ PID was etched down to the BOX.

## EXPERIMENTAL RESULTS

Figure 3 showcases the iCPID architecture. During operation, the gas mixture enters the inlet of the iCPID, and is subsequently separated by the  $\mu$ column whose temperature is ramped by the integrated heater. At the end of the  $\mu$ column, the separated molecules take path through the microfluidic via entering the  $\mu$ PID where they are detected non-destructively. This top-down architecture of the iCPID minimizes the overall footprint by allowing the  $\mu$ PID to be stacked directly on the  $\mu$ column while avoiding any off-chip interconnection in between.

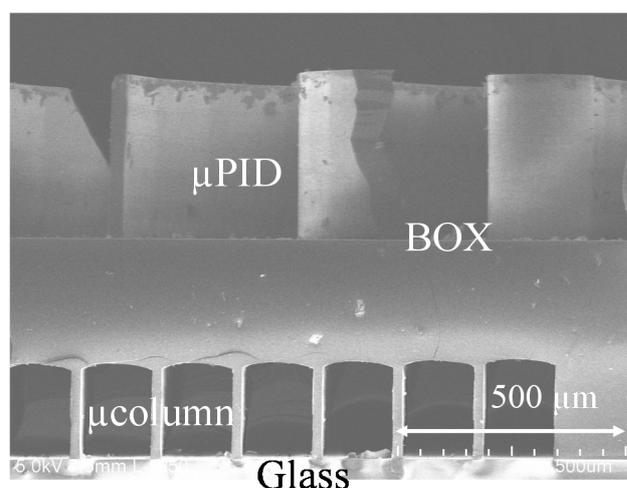


Figure 3: Scanning electron microscopy (SEM) of a cross-section of the iCPID featuring monolithically integrated  $\mu$ PID on  $\mu$ column.

The iCPID was coated with Polydimethylsiloxane (PDMS) non-polar stationary phase and packaged into an ultracompact  $\mu$ GC system, dubbed integrated cube (*i.e.*, iCube). The system consisted mainly of a stainless steel preconcentrator, an iCPID, a pump, an air filter, two microfabricated Y-connectors, two 3-port valves, a set of four 5500 mAh rechargeable batteries and an in-house control circuit board. Components were fluidically interconnected using flexible Polytetrafluoroethylene (PTFE) tubes and guard columns. The components and fluidic diagram for the iCube along with its operation are depicted in Figure 4(A). For iCube operation, the analytes were sampled from a gas storage bag into the preconcentrator before backflush injection into the iCPID. Ambient air, which was filtered through an inline filter to remove moisture and hydrocarbons, was used as the carrier gas at a flow rate of  $\sim 0.9$  mL/min. Separation was conducted isothermally at room temperature ( $\sim 22$   $^\circ\text{C}$ ). A representative chromatogram of a standard sample containing seven VOCs is shown in Figure 4(B), showing that separation can be completed within 100 s.

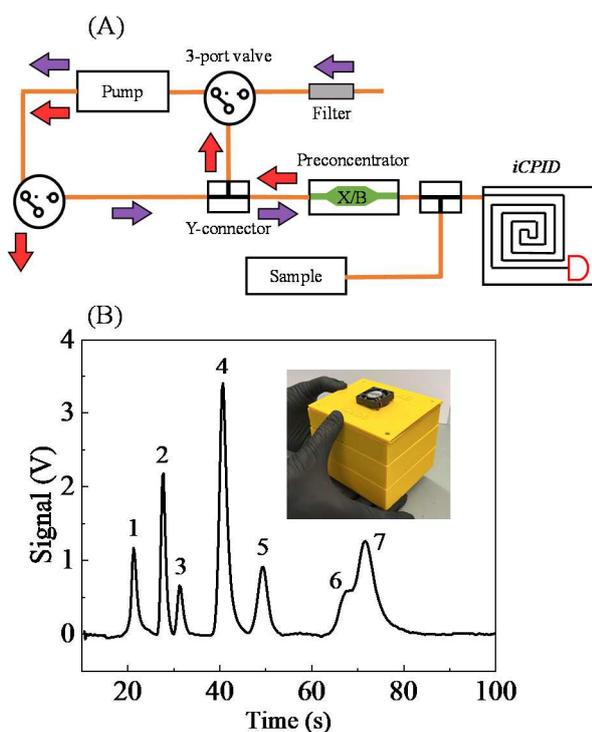


Figure 4: (A) System schematic of the ultracompact  $\mu$ GC device, named integrated Cube (i.e., iCube). The sampling and analyzing path are indicated with red and purple arrows respectively. (B) Chromatogram of (1) acetone, (2) benzene, (3) heptane, (4) toluene, (5) octane, (6) ethylbenzene, and (7) xylene generated by the iCube. Filtered air was used as the carrier gas with a flow rate of 0.9 mL/min. Inset shows the photograph of the iCube that occupies 0.9 liters and weighs 0.9 kg.

## DISCUSSION AND CONCLUSION

In summary, this work reports a monolithically integrated microfluidic photoionization detector ( $\mu$ PID) on a microfabricated gas chromatography ( $\mu$ GC) column via wafer-level batch processing on an SOI platform. Such device architecture provides a smaller chip footprint, more robust fluidic connection by eliminating off-chip interconnects, and potential reduced cost for future mass production on the wafer scale. The iCPID enables an ultracompact (0.9 liters and 0.9 kg), fully automated, and battery-operated  $\mu$ GC system. Rapid separation of seven volatile organic compounds (VOCs) in  $\sim$ 2 min at room temperature is demonstrated.

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